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Report:

In $(\gamma, e\gamma)$ -spectroscopy the measured intensity distributions are proportional to the 3-dimensional electron momentum density (EMD) of the investigated samples [1]. Experiments had already performed at different places showing the feasibility of these measurements. In the reported experiment it was possible for the very first time to measure the 3-dimensional EMD in a single experiment as a function of all 3 momentum components. This enhancement was due to the first use of a 2-dimensional electron detector and read-out electronics enabling the coincident detection of the energy of the Compton-scattered photon and 2 momentum components of the recoil electron. As a sample we choose a Si single crystal from which we wanted to obtain two complete 3D datasets. In the experiment the incident beam was monochromatized by means of a uncooled triangular Si crystal used in horizontal Bragg reflection from 551 planes. The asymmetric cut was 1.5° and the crystal was bent to about 500 μm thus focussing 23 mm of beam into a beamspot of ≈ 1 mm. The bandwidth was 0.5 % and a monochromatic flux of 3.7×10^{11} (5.7×10^{10}) ph/s/100 mA could be obtained at the sample for 139 and 180 keV, respectively. During the experiment we increased the incident energy in order to increase the energy of the recoil electrons. For the energy-resolved photon detection we used a single-element high purity Ge-detector with $\Delta E = 675$ eV at 140 keV. The electron detector is build of 33 Si-PIN-diodes, each 5 x 5 mm² and equipped with its own in-vacuum preamplifier and a rack-mounted main amplifier. The 2-dimensional detector matrix consists of 5 rows containing 5-7-9-7-5 elements. The pitch between the pixels is 10mm. in both directions. The energy resolution per pixel of $\approx 5 - 6$ keV is poor. The sample was a Si wafer with its surface normal parallel to the [100] direction and another [100] direction in the scattering plane. The wafer was etched in the center area to a thickness of 2.2 μm . In the experiment we oriented the surface normal $\pm 22.5^\circ$ to the scattering vector $\vec{K} = \vec{k}' - \vec{k}_0$ with momenta \vec{k}_0 (\vec{k}') of the incident (scattered) photon. Coincidence countrates were 2.8 Hz (150 mA) for 139 keV incident energy with single countrates of 0.15 kHz and 50 kHz in the photon and integral electron detector, respectively.

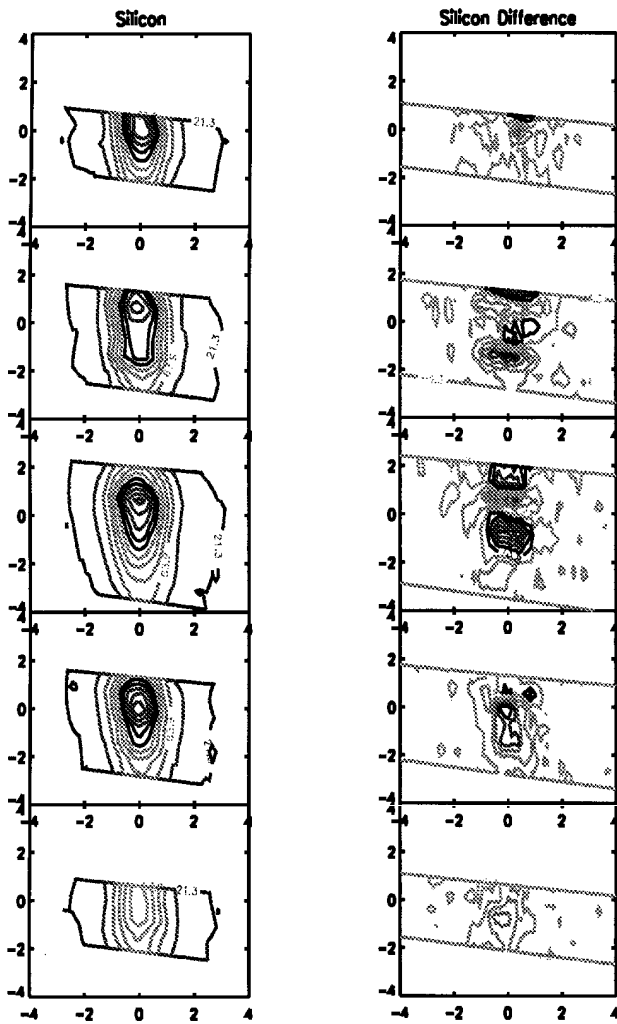


Figure: The left column shows contour plots of the 3D-EMD of Si in $p_x - p_x$ -planes. $p_y = [p_y^0 \zeta p_y^1 \zeta p_y^2 \zeta p_y^3 \zeta p_y^4]$ from top to bottom. In the right column contour plots of the difference-EMD are shown for the same momentum coordinates.

References

- [1] Th. Tschentscher, J.R. Schneider, F. Bell, Phys. Rev. B48, 16965(1993)
- [2] F.F. Kurp, A.E. Werner, J.R. Schneider, Th. Tschentscher, P. Suortti, F. Bell, submitted Nucl. Instrum. Methods A
- [3] C. Blaas, private communication, (1995)
- [4] S. Tanigawa, Hyperfine Interactions 79, 575(1993)

The figure shows as a result of the measurements the direction EMD of Si taken for one direction and the difference-EMD after subtraction of both directional measurements. The horizontal p_x -coordinate corresponds to the photon energy and the vertical p_x -coordinate is the horizontal component of the 2D-electron detector. The 5 plots reflect the 5 rows of detector pixels and stand therefore for different p_y -values. The inclination of the energy measurement when transformed to momentum coordinates is a consequence of purely kinematical considerations [2]. Due to the thickness of the Si sample special care has to be taken of the electron multiple scattering. The final analysis of the data will result in a difference map, which is to be compared with well established results of different experimental techniques and/or theoretical calculations [3, 4]. But even in the very preliminary difference-EMD shown here, maxima along the p_x -direction can be seen, which corresponds to the direction the sample had been turned.